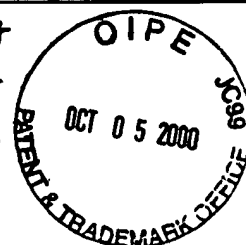


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INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. 970150A	Serial No. 09/228,148
	Applicant(s): Y. INOUE et al.	
	Filing Date: January 11, 1999	Group Art Unit: 2823

U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
<u>LB</u>	AA	5,024,723	Goesele et al.	06/1991	156 628	
<u>LB</u>	AB	5,314,843	Yu et al.	05/1994	437 225	
<u>LB</u>	AC	5,674,784	Jang et al.	10/1997	437 195	
<u>LB</u>	AD	5,616,513	Shepard	04/1997	438 402	
<u>LB</u>	AE	5,723,895	Takahashi	03/1998	251 499	
<u>LB</u>	AF	5,830,773	Brennan et al.	11/1998	437 67	
<u>LB</u>	AG	5,314,834	Mazure et al.	05/1994	437 43	
<u>LB</u>	AH	6,071,807	Watanabe et al.	06/2000	438 623	



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OTHER DOCUMENTS

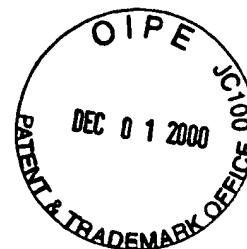
<u>LT</u>	AY	Wang et al. , "A Study of Plasma Treatments on Siloxane SOB," IEEE VMIC Conference, June 7-8, 1994, pp. 101-107
<u>LT</u>	AZ	Chiang et al., "Defects Study on Spin on Glass Planarization Technology, IEEE VMIC Conference, June 15-16, 1987, pp. 404-412.
<u>LB</u>	BA	Lai-Juh Chen, et al., "Fluorine-Implanted Treatment (FIT) SOG for the Non-Etchback Intermetal Dielectric," IEEE VMIC Conference, June 7-8, 1994, pp. 81-86.
<u>LB</u>	BB	Moriya et al., "Modification Effects in Ion-Implanted SiO ₂ Spin-on-Glass," <u>J. Electrochem. Soc.</u> , Vol. 140, No. 5, May 1993, pp. 1442-1450.
<u>LB</u>	BC	Matsuura et al., "An Advanced Interlayer Dielectric System with Partially Converted Organic SOG Using Plasma Treatment," IEEE VMIC Conference, June 8-9, 1993, pp. 113-115.
<u>LB</u>	BD	Ishida et al., "Mechanism for ALSiCu alloy Corrosion," <u>Jpn. J. Appl. Phys.</u> , Vol. 31 (1992), pp. 2045-2048.
<u>LB</u>	BE	Doki et al., "Moisture-Blocking Mechanism of ECR-Plasma," IEEE VMIC Conference, June 7-8, 1994, pp. 235-139.
<u>LB</u>	BF	Shimokawa et al., "Suppression of MOSFET hot carrier degradation by P-SiO underLayer," <u>The Institute of Electronics, Information and Communication Engineers</u> , Technical Report of IEICE, SDM92-133 (1992-12), pp. 89-94.
<u>LT</u>	BG	Murase et al., "Dielectric Constant of Silicon Dioxide Deposited by Atmospheric-Pressure Chemical Vapor Deposition Using Tetraethylorthosilicate and Ozone," <u>Jpn. J. Appl. Phys.</u> , Vol. 33 (1994), pp. 1385-1389.

Examiner <u>Kurt Eaton</u>	Date Considered <u>2/13/01</u>
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INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. 970150A	Serial No. 09/228,148
	Applicant(s): Y. INOUE et al.	
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U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
<u>16</u>	AA	5,892,269	Y. Inoue et al.	04/99	257	634
<u>16</u>	AB	5,404,046	Matsumoto et al.	04/95	257	750
<u>16</u>	AC	5,898,221	Mizuhara et al.	04/99	257	751
_____	AD					
_____	AE					
_____	AF					



Examiner Kurt Eaton	Date Considered 3/13/01
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